

ABSTRACT OF THE DISCLOSURE

Wiring layers through that come into direct contact with an electrode of a ferroelectric capacitor provide a wiring layer structure configured so that the characteristic of the ferroelectric substance is not degraded by production of a reducing agent. One of coating layers through is provided on the periphery of the Al main wiring layer. A single Ti film or TiN film or a combination of both is used as the coating film. The TiN film suppresses reaction between water and aluminum. The Ti film occludes hydrogen. Therefore, the coating layer provided on the periphery of the Al wiring layer inhibits water or molecular hydrogen from entering the Al wiring layer from the outside and therefore there is no degradation of the characteristics of the ferroelectric capacitor.

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